**Product data sheet** 

## 1. General description

N-channel enhancement mode Field-Effect Transistor (FET) in a small SOT23 (TO-236AB) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

## 2. Features and benefits

- Low threshold voltage
- Extended temperature range T<sub>i</sub> = 175 °C
- Trench MOSFET technology
- ElectroStatic Discharge (ESD) protection > 500 V HBM (class H1B)
- AEC-Q101 qualified

## 3. Applications

- Relay driver
- High-speed line driver
- · Low-side load switch
- · Switching circuits

## 4. Quick reference data

#### Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> = 25 °C		-	-	20	V
$V_{GS}$	gate-source voltage			-8	-	8	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = 4.5 V; T <sub>amb</sub> = 25 °C	[1]	-	-	7	Α
Static charac	teristics		·				
R <sub>DSon</sub>	drain-source on-state resistance	$V_{GS} = 4.5 \text{ V}; I_D = 7 \text{ A}; T_j = 25 ^{\circ}\text{C}$		-	15	19	mΩ

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and mounting pad for drain 6 cm<sup>2</sup>.



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# 5. Pinning information

### **Table 2. Pinning information**

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		D
2	S	source	3	
3	D	drain	SOT23	G S 017aaa255

# 6. Ordering information

### **Table 3. Ordering information**

Type number	Package				
	Name	Description	Version		
PMV15UNEA		plastic, surface-mounted package; 3 terminals; 1.9 mm pitch; 2.9 mm x 1.3 mm x 1 mm body	SOT23		

# 7. Marking

### Table 4. Marking codes

Type number	Marking code[1]
PMV15UNEA	%GN

[1] % = placeholder for manufacturing site code

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## 8. Limiting values

#### **Table 5. Limiting values**

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> = 25 °C		-	20	V
V <sub>GS</sub>	gate-source voltage			-8	8	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = 4.5 V; T <sub>amb</sub> = 25 °C	[1]	-	7	А
		V <sub>GS</sub> = 4.5 V; T <sub>amb</sub> = 100 °C	[1]	-	4.4	Α
I <sub>DM</sub>	peak drain current	$T_{amb}$ = 25 °C; single pulse; $t_p \le 10 \mu s$		-	28	А
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> = 25 °C	[2]	-	610	mW
			[1]	-	1.4	W
		T <sub>sp</sub> = 25 °C		-	8.3	W
Tj	junction temperature			-55	175	°C
T <sub>amb</sub>	ambient temperature			-55	175	°C
T <sub>stg</sub>	storage temperature			-65	175	°C
Source-drain d	iode		•	'		
Is	source current	T <sub>amb</sub> = 25 °C	[1]	-	1.4	Α
ESD maximum	rating					
V <sub>ESD</sub>	electrostatic discharge voltage	НВМ	[3]	-	500	V
Avalanche rug	gedness		-	'		,
E <sub>DS(AL)S</sub>	non-repetitive drain- source avalanche energy	T <sub>j(init)</sub> = 25 °C; I <sub>D</sub> = 1.5 A; DUT in avalanche (unclamped)		-	14	mJ

- [1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and mounting pad for drain  $^2$ .
- [2] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.
- [3] Measured between all pins.

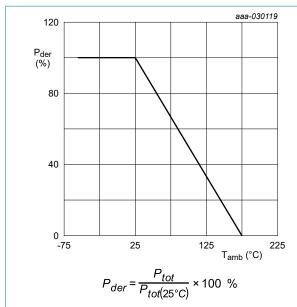


Fig. 1. Normalized total power dissipation as a function of ambient temperature

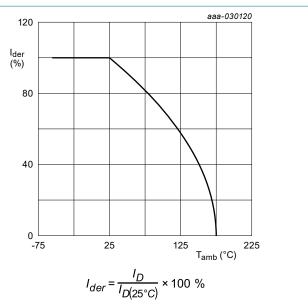


Fig. 2. Normalized continuous drain current as a function of ambient temperature

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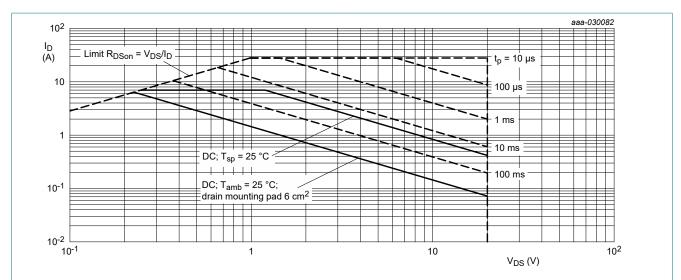


Fig. 3. Safe operating area; junction to ambient; continuous and peak drain currents as a function of drain-source voltage

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## 9. Thermal characteristics

**Table 6. Thermal characteristics** 

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R <sub>th(j-a)</sub>	thermal resistance from	in free air	[1]	-	208	245	K/W
junction to	junction to ambient	n to ambient	[2]	-	88	104	K/W
$R_{th(j-sp)}$	thermal resistance from junction to solder point			-	13	18	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and mounting pad for drain 6 cm<sup>2</sup>.

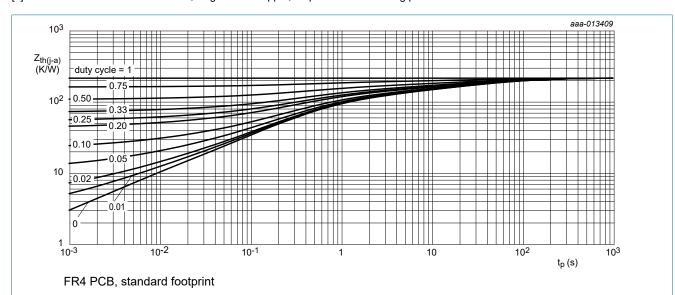


Fig. 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

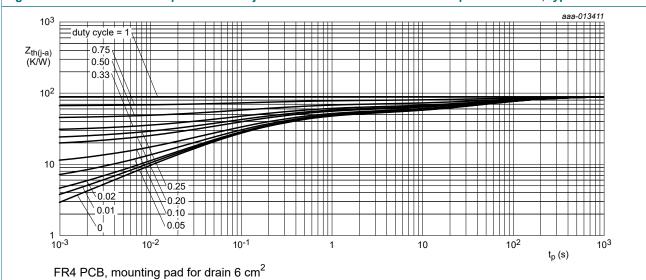


Fig. 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

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## 10. Characteristics

#### **Table 7. Characteristics**

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics					
V <sub>(BR)DSS</sub>	drain-source breakdown voltage	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = 25 °C$	20	-	-	V
$V_{GSth}$	gate-source threshold voltage	$I_D = 250 \mu A; V_{DS} = V_{GS}; T_j = 25 \text{ °C}$	0.4	0.65	0.9	V
I <sub>DSS</sub>	drain leakage current	V <sub>DS</sub> = 20 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	1	μΑ
I <sub>GSS</sub>	gate leakage current	V <sub>GS</sub> = 8 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	10	μΑ
		V <sub>GS</sub> = -8 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	-10	μΑ
R <sub>DSon</sub>	drain-source on-state	V <sub>GS</sub> = 4.5 V; I <sub>D</sub> = 7 A; T <sub>j</sub> = 25 °C	-	15	19	mΩ
	resistance	V <sub>GS</sub> = 4.5 V; I <sub>D</sub> = 7 A; T <sub>j</sub> = 175 °C	-	28	35	mΩ
		$V_{GS} = 2.5 \text{ V}; I_D = 5.7 \text{ A}; T_j = 25 \text{ °C}$	-	18	24	mΩ
		V <sub>GS</sub> = 1.8 V; I <sub>D</sub> = 2 A; T <sub>j</sub> = 25 °C	-	23	36	mΩ
9 <sub>fs</sub>	forward transconductance	$V_{DS} = 10 \text{ V}; I_D = 7 \text{ A}; T_j = 25 \text{ °C}$	-	50	-	S
$R_G$	gate resistance	f = 1 MHz	-	2	-	Ω
Dynamic ch	aracteristics		'			1
Q <sub>G(tot)</sub>	total gate charge	V <sub>DS</sub> = 10 V; I <sub>D</sub> = 6 A; V <sub>GS</sub> = 4.5 V;	-	11	17	nC
Q <sub>GS</sub>	gate-source charge	T <sub>j</sub> = 25 °C	-	1.3	-	nC
$Q_{GD}$	gate-drain charge		-	2.1	-	nC
C <sub>iss</sub>	input capacitance	V <sub>DS</sub> = 10 V; f = 1 MHz; V <sub>GS</sub> = 0 V;	-	1220	-	pF
C <sub>oss</sub>	output capacitance	T <sub>j</sub> = 25 °C	-	124	-	pF
C <sub>rss</sub>	reverse transfer capacitance		-	102	-	pF
t <sub>d(on)</sub>	turn-on delay time	V <sub>DS</sub> = 10 V; I <sub>D</sub> = 6 A; V <sub>GS</sub> = 4.5 V;	-	10	-	ns
t <sub>r</sub>	rise time	$R_{G(ext)} = 6 \Omega; T_j = 25 °C$	-	24	-	ns
t <sub>d(off)</sub>	turn-off delay time		-	32	-	ns
t <sub>f</sub>	fall time	]	-	34	-	ns
Source-drai	in diode					•
$V_{SD}$	source-drain voltage	$I_S = 1.4 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C}$	-	0.7	1.2	V
t <sub>rr</sub>	reverse recovery time	$I_S = 1.5 \text{ A}; dI_S/dt = -100 \text{ A/µs};$	-	10	-	ns
Q <sub>r</sub>	recovered charge	$V_{GS} = 0 \text{ V}; V_{DS} = 10 \text{ V}; T_j = 25 \text{ °C}$	-	2	-	nC

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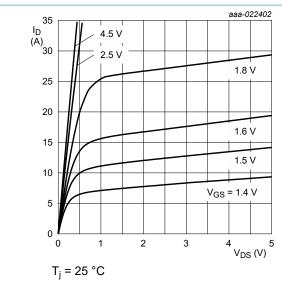


Fig. 6. Output characteristics: drain current as a function of drain-source voltage; typical values

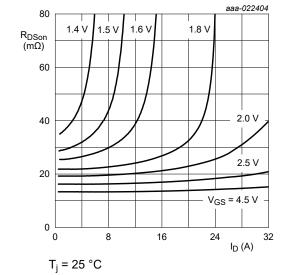
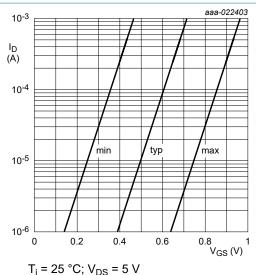


Fig. 8. Drain-source on-state resistance as a function of drain current; typical values



 $I_j = 25 \text{ C}; V_{DS} = 5 \text{ V}$ 

Fig. 7. Sub-threshold drain current as a function of gate-source voltage

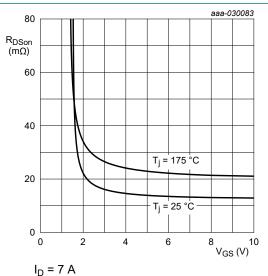


Fig. 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

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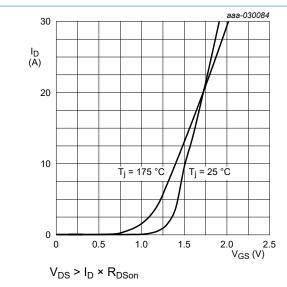


Fig. 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values

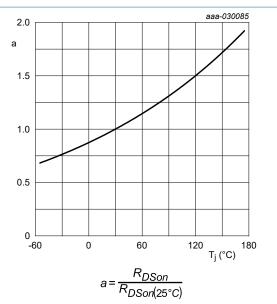


Fig. 11. Normalized drain-source on-state resistance as a function of junction temperature; typical values

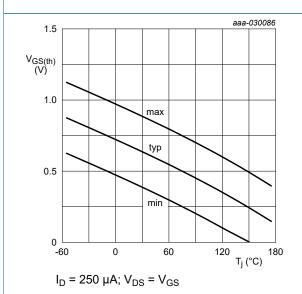


Fig. 12. Gate-source threshold voltage as a function of junction temperature

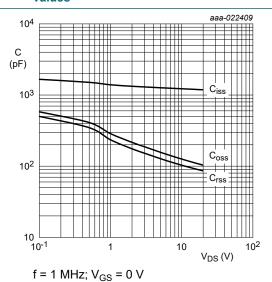


Fig. 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

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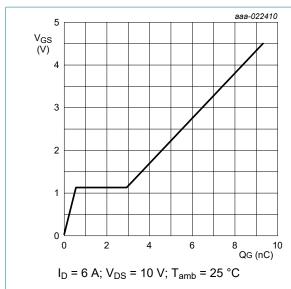


Fig. 14. Gate-source voltage as a function of gate charge; typical values

 $V_{GS} = 0 V$ 

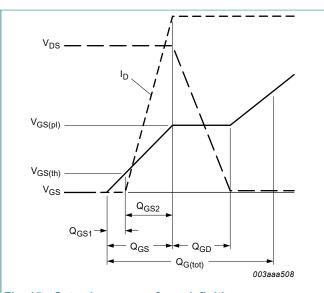


Fig. 15. Gate charge waveform definitions

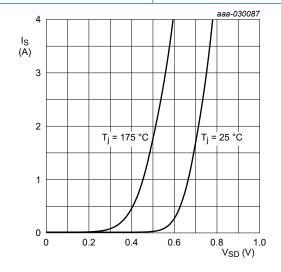
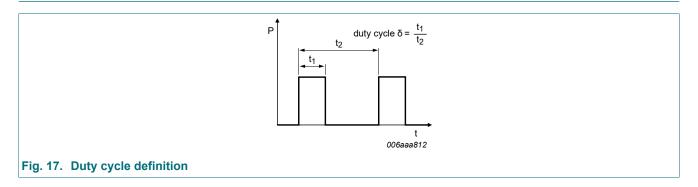


Fig. 16. Source current as a function of source-drain voltage; typical values

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## 11. Test information



## **Quality information**

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101 - Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

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## 12. Package outline

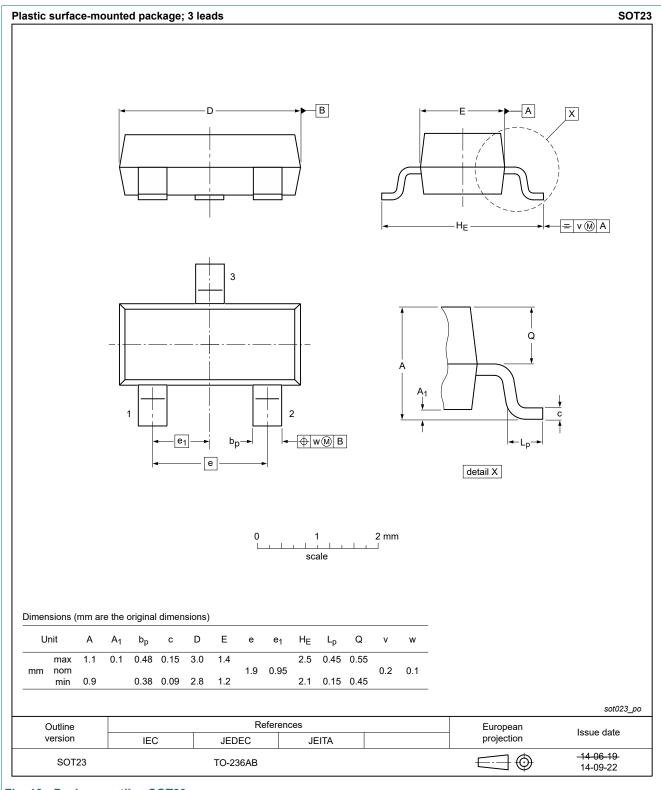
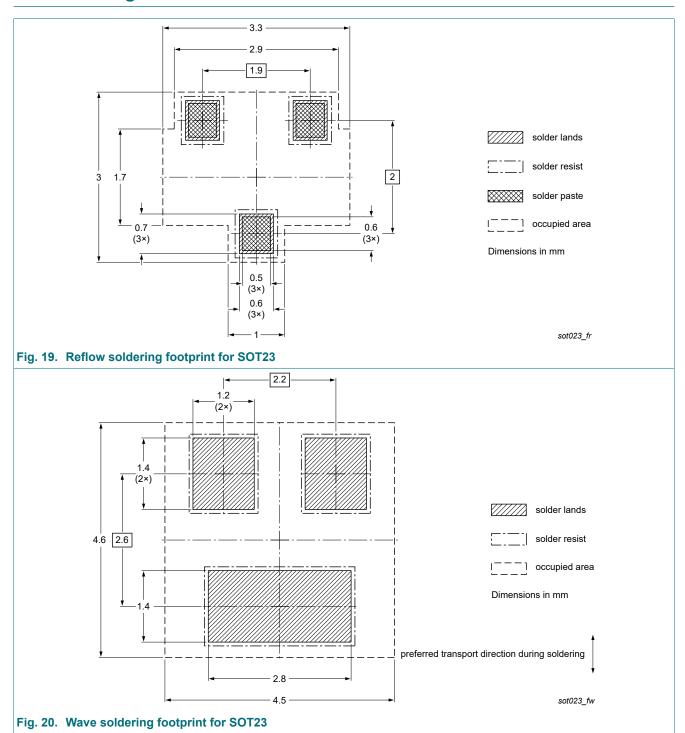


Fig. 18. Package outline SOT23

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## 13. Soldering



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# 14. Revision history

#### **Table 8. Revision history**

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes				
PMV15UNEA v.2	20240812	Product data sheet	-	PMV15UNEA v.1				
Modifications:	Chapter "Characteris	Chapter "Characteristics": Fig. 16, label of the vertical axis corrected						
PMV15UNEA v.1	20190906	Product data sheet	-	-				

### 20 V, N-channel Trench MOSFET

## 15. Legal information

#### **Data sheet status**

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions".
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